TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM10LZ47

AC POWER CONTROL APPLICATIONS

• Repetitive Peak Off–State Voltage : $V_{DRM} = 800V$ • R.M.S. On–State Current : $I_{T (RMS)} = 10A$

High Commutation (dv / dt)

• Isolation Voltage : V_{ISOL} = 1500V AC

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage	V_{DRM}	800	V	
R.M.S On-State Current (Full Sine Waveform)	I _{T (RMS)}	10	А	
Peak One Cycle Surge On-State	l-o	100 (50Hz)	А	
Current (Non-Repetitive)	ITSM	110 (60Hz)		
I ² t Limit Value	ı²t	50	A ² s	
Critical Rate of Rise of On-State Current (Note)	di / dt	50	A / μs	
Peak Gate Power Dissipation	P _{GM}	5	W	
Average Gate Power Dissipation	P _{G (AV)}	0.5	W	
Peak Gate Voltage	V_{FGM}	10	V	
Peak Gate Current	I _{GM}	2	Α	
Junction Temperature	Tj	-40~125	°C	
Storage Temperature Range	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t = 1min.)	V _{ISOL}	1500	V	

Weight: 1.7g

Note: di / dt test condition

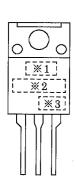
 $V_{DRM} = 0.5 \times Rated$, $I_{TM} \le 15A$, $t_{gw} \ge 10 \mu s$,

 $t_{gr} \le 250$ ns, $i_{gp} = I_{GT} \times 2.0$

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT
Repetitive Peak Off-State Current		I _{DRM}	V _{DRM} = Rated		_	_	20	μΑ
Gate Trigger Voltage	I			T2 (+) , Gate (+)	_	_	1.5	V
	II	V_{GT}	$V_D = 12V$, $R_L = 20\Omega$	T2 (+) , Gate (−)	_	_	1.5	
	III		_	T2 (-) , Gate (-)	_	_	1.5	
Gate Trigger Current	I		$V_D = 12V$, $R_1 = 20\Omega$	T2 (+) , Gate (+)	_	_	30	mA
	II	I_{GT}		T2 (+) , Gate (-)	_	_	30	
	III		_	T2 (-) , Gate (-)	_	_	30	
Peak On-State Voltage		V _{TM}	I _{TM} = 15A		_	_	1.5	V
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V
Holding Current I _H		lн	V _D = 12V, I _{TM} = 1A		_	_	50	mA
Thermal Resistance Rth (j-c)		R _{th (j-c)}	Junction to Case, AC		_	_	3.4	°C/W
Critical Rate of Rise of Off-State Voltage dv / dt		dv / dt	V _{DRM} = 600V, T _j = 125°C Exponential Rise		_	300	_	V / µs
Critical Rate of Rise of Off–State Voltage at Commutation (dv / dt) c		(dv / dt) c	V _{DRM} = 400V, T _j = 125°C (di / dt) c = - 5.5A / ms		10		_	V / µs

MARKING



NUMBER	SYM	MARK	
*1	TOSHIBA PRODUCT MAR	5	
*2	TYPE	SM10LZ47	M10LZ47
*3	Lot Number Month (Starting from Alphabet A) Year (Last Decimal Digit of the Current Year)		Example 8A: January 1998 8B: February 1998 8L: December 1998

2 2001-07-10

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